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(54) LIGHT EMITTING ELEMENT AND METHOD OF MANUFACTURING SAME

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(57)ABSTRACT

A light emitting element comprises a semiconductor structure which includes an n-side layer, a p-side layer, and an ultraviolet light emitting active layer positioned between the n-side layer and the p-side layer, each being made of a nitride semiconductor, an n-electrode electrically connected to the n-side layer, and a p-electrode electrically connected to the p-side layer. The active layer has a well layer containing Al, a barrier layer containing Al, and holes defined by the lateral faces of the well layer and the lateral faces of the barrier layer. The p-side layer has a first layer containing Al, a second layer containing Al disposed on the first layer and in contact with the lateral faces of the well layer, and a third layer disposed on the second layer. The third layer is smaller in thickness than the first layer.

